

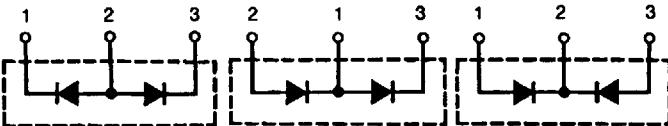
Fast Recovery Epitaxial Diode (FRED) Modules

MEA 140-12DA
MEE 140-12DA
MEK 140-012DA

$I_{FAVM} = 137 \text{ A}$
 $V_{RRM} = 1200 \text{ V}$
 $t_{rr} = 450 \text{ ns}$

Preliminary data

V_{RSM} V	V_{RRM} V	Type	MEA 140-12DA	MEE 140-12DA	MEK 140-012DA
1200	1200		1 2 3	2 1 3	1 2 3



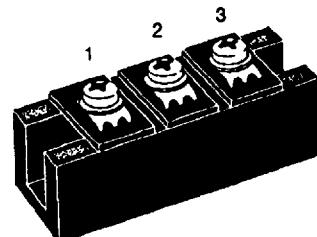
Symbol	Test Conditions		Maximum Ratings	
I_{FRMS}	$T_{vj} = 125^\circ\text{C}$	$T_s = 65^\circ\text{C}$	194	A
I_{FAVM} ①	$T_{vj} = 125^\circ\text{C}$	$T_s = 65^\circ\text{C}$; rectangular, $d = 0.5$	137	A
I_{FM}	$T_{vj} = 125^\circ\text{C}$	$T_s = 65^\circ\text{C}$	550	A
I_{FSM}	$T_{vj} = 45^\circ\text{C}$	$t = 10 \text{ ms}$ (50 Hz), sine	1200	A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	1280	A
	$T_{vj} = 150^\circ\text{C}$	$t = 10 \text{ ms}$ (50 Hz), sine	1080	A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	1190	A
$\int i^2 dt$	$T_{vj} = 45^\circ\text{C}$	$t = 10 \text{ ms}$ (50 Hz), sine	7200	A^2s
		$t = 8.3 \text{ ms}$ (60 Hz), sine	6800	A^2s
	$T_{vj} = 150^\circ\text{C}$	$t = 10 \text{ ms}$ (50 Hz), sine	5800	A^2s
		$t = 8.3 \text{ ms}$ (60 Hz), sine	5900	A^2s
T_{vj}	$T_s = 25^\circ\text{C}; T_{vj} = 150^\circ\text{C}$		-40...+150	°C
T_{sag}	$T_s = 25^\circ\text{C}$		-40...+125	°C
T_{smax}	$T_s = 65^\circ\text{C}$		110	°C
P_{tot}	$T_s = 25^\circ\text{C}; T_{vj} = 150^\circ\text{C}$		550	W
V_{ISOL}	50/60 Hz, RMS	$t = 1 \text{ min}$	3000	V~
	$I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ s}$	3600	V~
M_d	Mounting torque (M6)		2.25-2.75/20-25	Nm/lb.in.
	Terminal connection torque (M6)		4.5-5.5/40-48	Nm/lb.in.
d_s	Creeping distance on surface		12.7	mm
d_A	Strike distance through air		9.6	mm
a	Maximum allowable acceleration		50	m/s^2
Weight			150	g

Symbol	Test Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{vj} = 25^\circ\text{C}$ $V_R = V_{RRM}$	12	mA
	$T_{vj} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	3	mA
	$T_{vj} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$	60	mA
V_F	$I_F = 150 \text{ A}$; $T_{vj} = 125^\circ\text{C}$	1.53	V
	$T_{vj} = 25^\circ\text{C}$	1.81	V
	$I_F = 260 \text{ A}$; $T_{vj} = 125^\circ\text{C}$	1.15	V
	$T_{vj} = 25^\circ\text{C}$	2.01	V
V_{TO}	For power-loss calculations only	1.15	V
r_T	$T_{vj} = 125^\circ\text{C}$; $I_{F1} = 150 \text{ A}$; $I_{F2} = 260 \text{ A}$	2.34	$\text{m}\Omega$
R_{thJS}		0.228	K/W
t_{rr}	$I_F = 150 \text{ A}$	450	ns
I_{RM}	$V_R = 600 \text{ V}$	500	ns
	$-di/dt = 400 \text{ A}/\mu\text{s}$	45	A
		68	A

① I_{FAVM} rating includes reverse blocking losses at T_{vjM} , $V_R = 0.6 \text{ V}_{RRM}$, duty cycle $d = 0.5$

Data according to DIN/IEC 747

IXYS reserves the right to change limits, test conditions and dimensions



Features

- International standard package with DCB ceramic base plate
- Planar passivated chips
- Short recovery time
- Low switching losses
- Soft recovery behaviour
- Isolation voltage 3600 V~
- UL registered E 72873

Applications

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions in mm (1 mm = 0.0394")

